

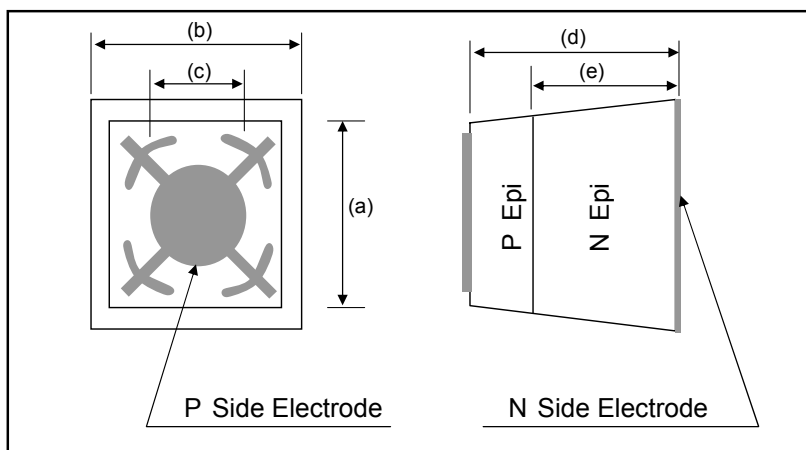
- 1. Material** Substrate GaAlAs (P Type) Removed  
Epitaxial Layer GaAlAs (N/P Type)
- 2. Electrode** N(Cathode) Side Gold Alloy  
P(Anode) Side Gold Alloy

**3. Electro-Optical Characteristics**

Parameter	Symbol	Min	Typ	Max	Unit	Condition
Forward Voltage	$V_{F(1)}$		1.1		V	IF=10uA
	$V_{F(2)}$		1.6	1.8	V	IF=100mA
Reverse Voltage	$V_R$	5			V	IR=10uA
Power	$P_O$		12.5		mW	IF=50mA
Wavelength	$\lambda_P$		880		nm	IF=50mA
	$\Delta\lambda$		45		nm	IF=50mA
Rise Time	$T_r$		28		ns	
Fall Time	$T_f$		20		ns	

※ Note : Power is measured by Sorter E/T system with bare chip.

- 4. Mechanical Data** (a) Emission Area ----- 14.7mil x 14.7mil
- (b) Bottom Area ----- 15.7mil x 15.7mil
- (c) Bonding Pad ----- 130um
- (d) Chip Thickness ----- 4mil
- (e) Junction Height ----- 4.6mil



**AUK Corp.**

Eoyang factory, 513-5 Eoyang-dong, Iksan, 570-210, Korea  
Tel. +82 63 839 1111 Fax. +82 63 835 8259

[www.auk.co.kr](http://www.auk.co.kr)

